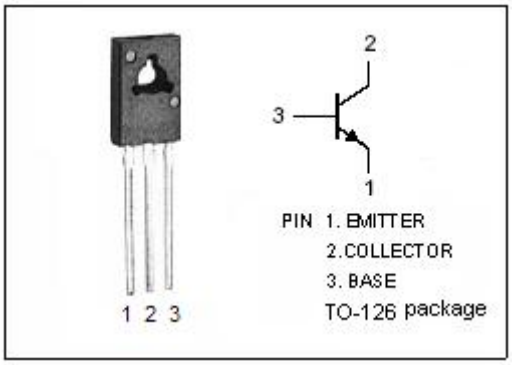
isc Silicon NPN Power Transistor 2SC3502

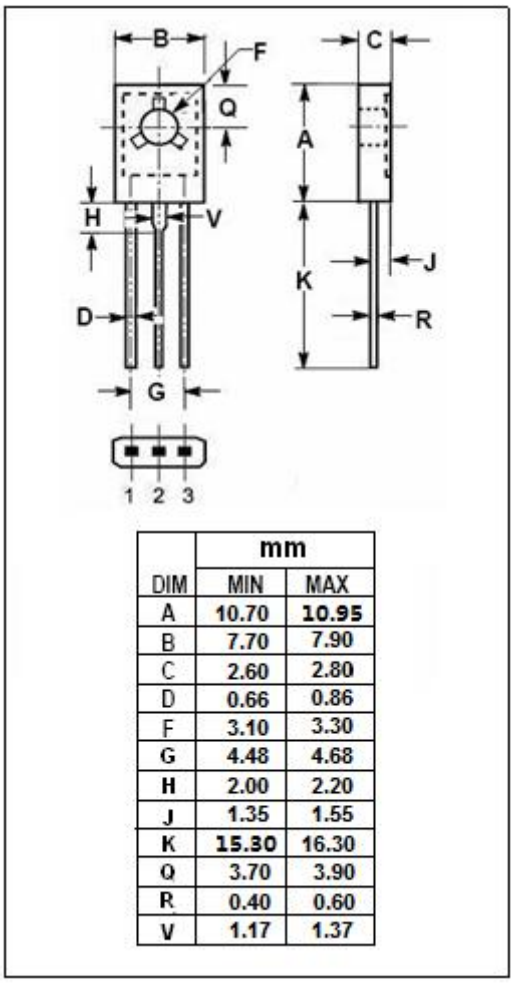


DESCRIPTION

- Collector–Emitter Breakdown Voltage—
  : $V_{(BR)CEO}$ = 200 V
- Complement to Type 2SA1380
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for ultrahigh-definition CRT display, video output applicaitons



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	0.1	A
I_{CM}	Collector Current-Peak	0.2	A
P_C	Collector Power Dssipation T_a=25℃	1.2	W
	Collector Power Dssipation T_C=25℃	5	
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 10 μ A ; I_E= 0	200			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 1mA ; R_{BE}= ∞	200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown VItage	I_E= 10 μ A ; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 20mA ;I_B= 2mA			0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 20mA ;I_B= 2mA			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 150V; I_E= 0			0.1	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0			0.1	μ A
h_{FE}	DC Current Gain	I_C= 10m A ; V_{CE}= 10V	40		320	
f_T	Current-Gain—Bandwidth Product	I_C= 10mA; V_{CE}= 30V;		150		MHz
C_{OB}	Collector Capacitance	I_E= 0; V_{CB}= 30V;f_{test} = 1MHz		1.7		pF

◆ **h_{FE} Classifications**

C	D	E	F
40-80	60-120	100-200	160-320